



ON Semiconductor®

FQD3P50TM-F085

500V P-Channel MOSFET

General Description

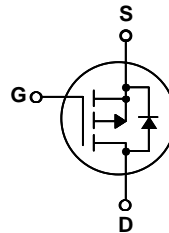
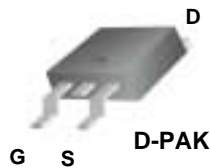
These P-Channel enhancement mode power field effect transistors are produced using ON Semiconductor's proprietary, planar stripe, DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for electronic lamp ballast based on complimentary half bridge.

Features

- -2.1A, -500V, $R_{DS(on)} = 4.9\Omega @ V_{GS} = -10V$
- Low gate charge (typical 18 nC)
- Low Crss (typical 9.5 pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability
- Qualified to AEC Q101
- RoHS Compliant



FQD3P50TM-F085 500V P-Channel MOSFET



Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Parameter	FQD3P50TM-F085	Units
V _{DSS}	Drain-Source Voltage	-500	V
I _D	Drain Current - Continuous (T _C = 25°C) - Continuous (T _C = 100°C)	-2.1	A
		-1.33	A
I _{DM}	Drain Current - Pulsed (Note 1)	-8.4	A
V _{GSS}	Gate-Source Voltage	± 30	V
E _{AS}	Single Pulsed Avalanche Energy (Note 2)	250	mJ
I _{AR}	Avalanche Current (Note 1)	-2.1	A
E _{AR}	Repetitive Avalanche Energy (Note 1)	5.0	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	-4.5	V/ns
P _D	Power Dissipation (T _A = 25°C) *	2.5	W
	Power Dissipation (T _C = 25°C) - Derate above 25°C	50	W
		0.4	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +150	°C
T _L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	°C

Thermal Characteristics

Symbol	Parameter	Typ	Max	Units
R _{θJC}	Thermal Resistance, Junction-to-Case	--	2.5	°C/W
R _{θJA}	Thermal Resistance, Junction-to-Ambient *	--	50	°C/W
R _{θJA}	Thermal Resistance, Junction-to-Ambient	--	110	°C/W

* When mounted on the minimum pad size recommended (PCB Mount)

Electrical Characteristics

$T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off Characteristics

BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = -250\ \mu\text{A}$	-500	--	--	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = -250\ \mu\text{A}$, Referenced to 25°C	--	0.42	--	$\text{V}/^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -500\text{ V}, V_{GS} = 0\text{ V}$	--	--	-1	μA
		$V_{DS} = -400\text{ V}, T_C = 125^\circ\text{C}$	--	--	-10	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250\ \mu\text{A}$	-3.0	--	-5.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = -10\text{ V}, I_D = -1.05\text{ A}$	--	3.9	4.9	Ω
g_{FS}	Forward Transconductance	$V_{DS} = -50\text{ V}, I_D = -1.05\text{ A}$ (Note 4)	--	2.1	--	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = -25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	510	660	pF
C_{oss}	Output Capacitance		--	70	90	pF
C_{rss}	Reverse Transfer Capacitance		--	9.5	12	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = -250\text{ V}, I_D = -2.7\text{ A},$ $R_G = 25\ \Omega$	--	12	35	ns	
t_r	Turn-On Rise Time		--	56	120	ns	
$t_{d(off)}$	Turn-Off Delay Time		(Note 4, 5)	--	35	80	ns
t_f	Turn-Off Fall Time		(Note 4, 5)	--	45	100	ns
Q_g	Total Gate Charge	$V_{DS} = -400\text{ V}, I_D = -2.7\text{ A},$ $V_{GS} = -10\text{ V}$	--	18	23	nC	
Q_{gs}	Gate-Source Charge		(Note 4, 5)	--	3.6	--	nC
Q_{gd}	Gate-Drain Charge		(Note 4, 5)	--	9.2	--	nC

Drain-Source Diode Characteristics and Maximum Ratings

I_S	Maximum Continuous Drain-Source Diode Forward Current	--	--	-2.1	A	
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current	--	--	-8.4	A	
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = -2.1\text{ A}$	--	--	-5.0	V
t_{rr}	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_S = -2.7\text{ A},$	--	270	--	ns
Q_{rr}	Reverse Recovery Charge	$di_F / dt = 100\text{ A}/\mu\text{s}$ (Note 4)	--	1.5	--	μC

Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. $L = 102\text{mH}, I_{AS} = -2.1\text{ A}, V_{DD} = -50\text{ V}, R_G = 25\ \Omega$, Starting $T_J = 25^\circ\text{C}$
3. $I_{SD} \leq -2.7\text{ A}, di/dt \leq 200\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse width $\leq 300\ \mu\text{s}$, Duty cycle $\leq 2\%$
5. Essentially independent of operating temperature

Typical Characteristics

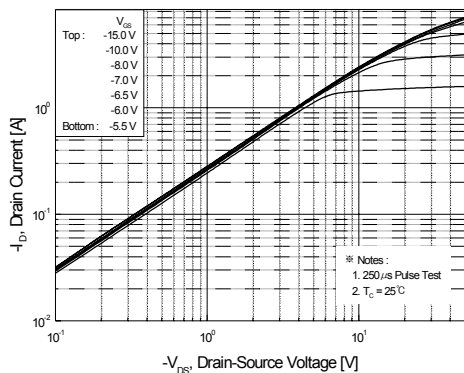


Figure 1. On-Region Characteristics

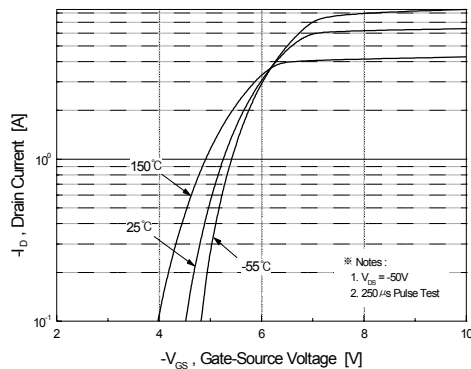


Figure 2. Transfer Characteristics

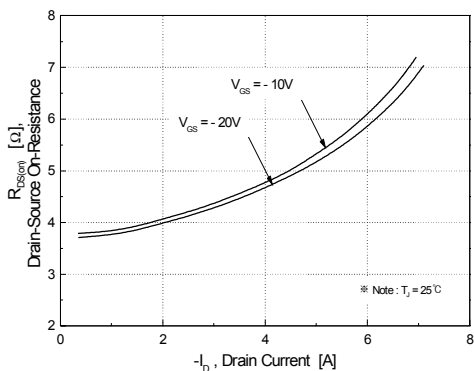


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

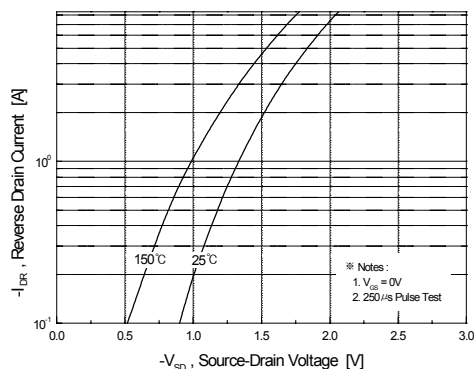


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

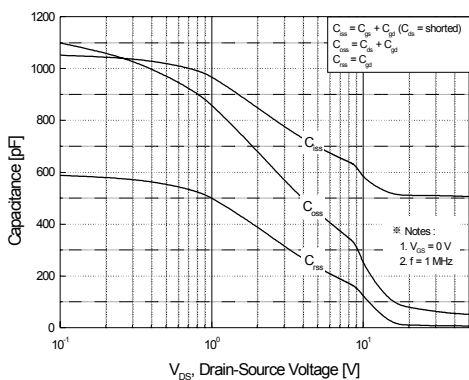


Figure 5. Capacitance Characteristics

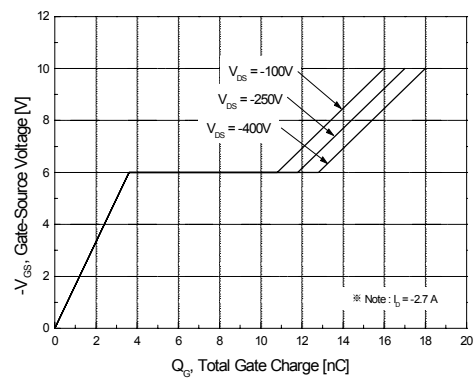


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

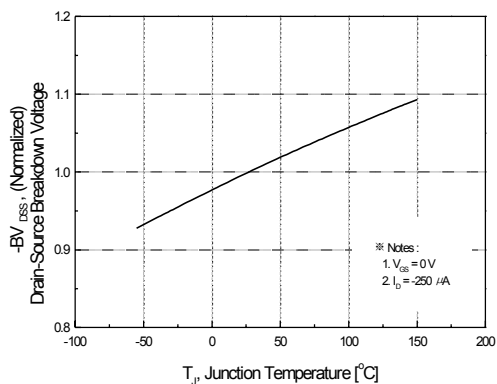


Figure 7. Breakdown Voltage Variation vs. Temperature

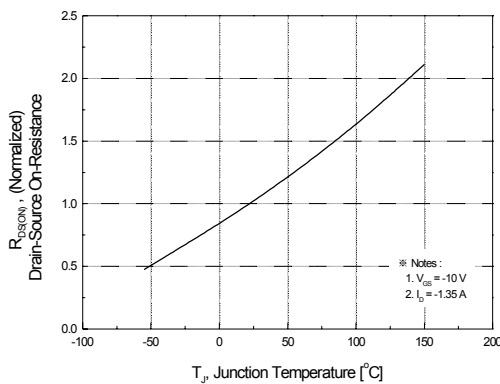


Figure 8. On-Resistance Variation vs. Temperature

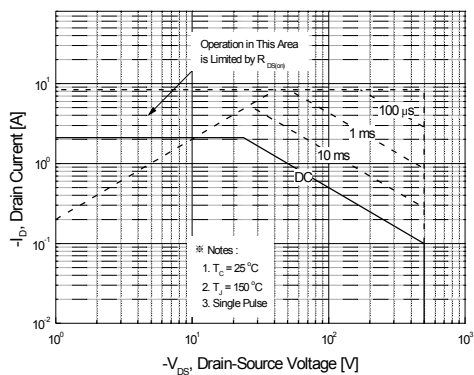


Figure 9. Maximum Safe Operating Area

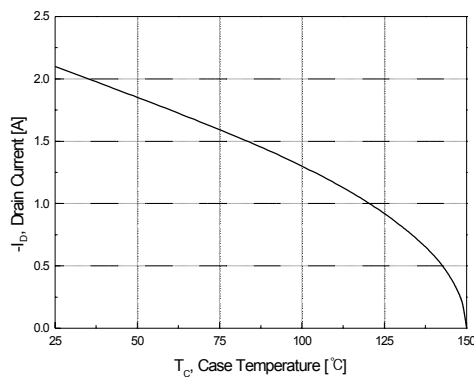


Figure 10. Maximum Drain Current vs. Case Temperature

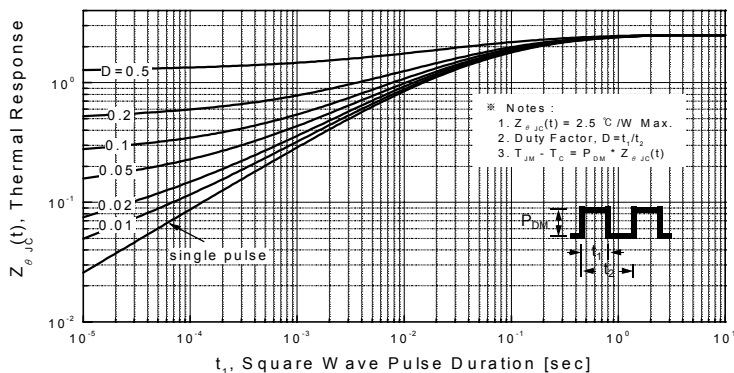
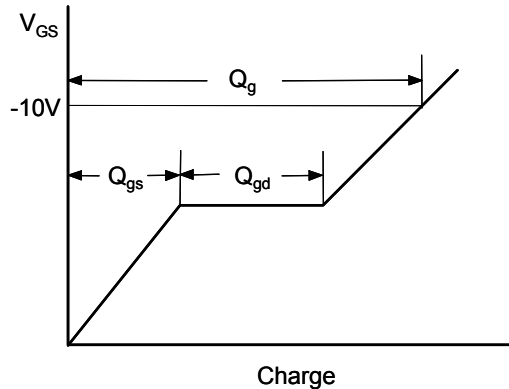
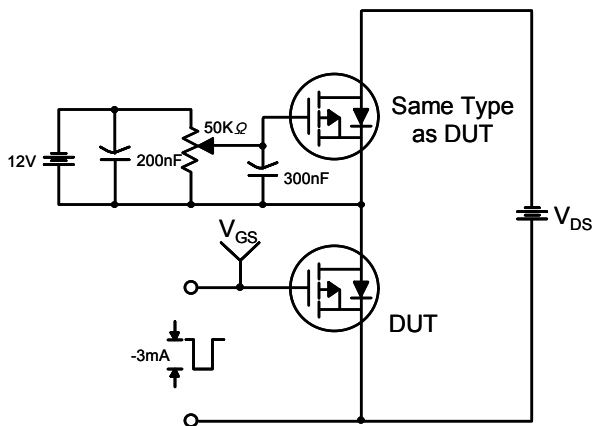
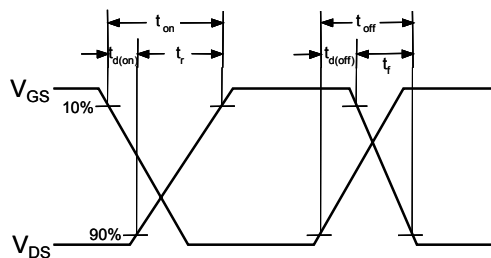
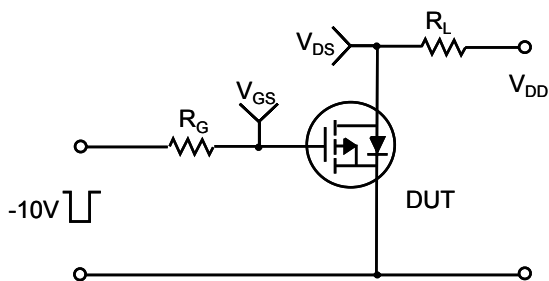


Figure 11. Transient Thermal Response Curve

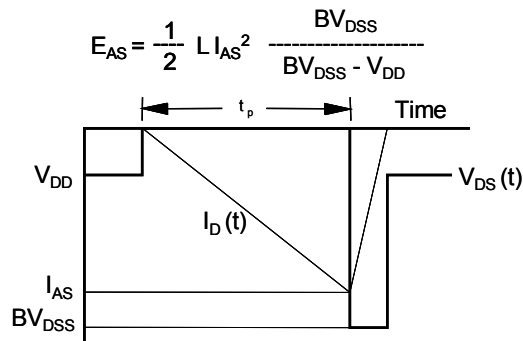
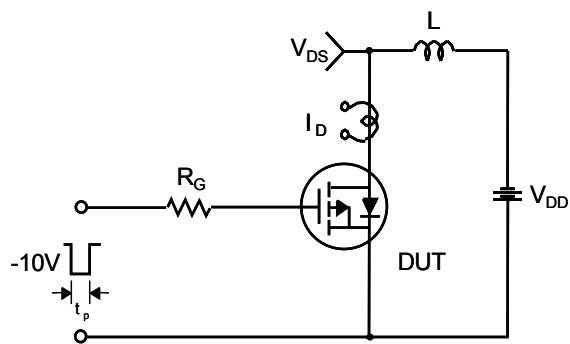
Gate Charge Test Circuit & Waveform



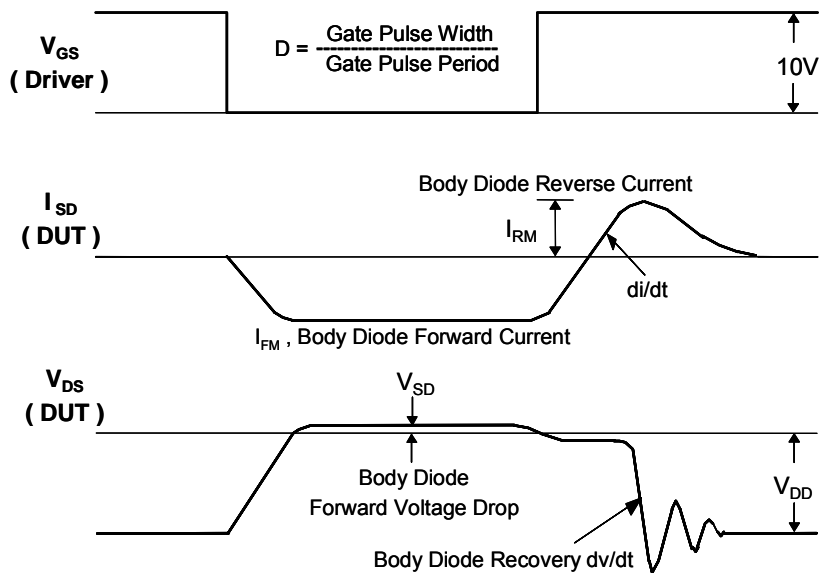
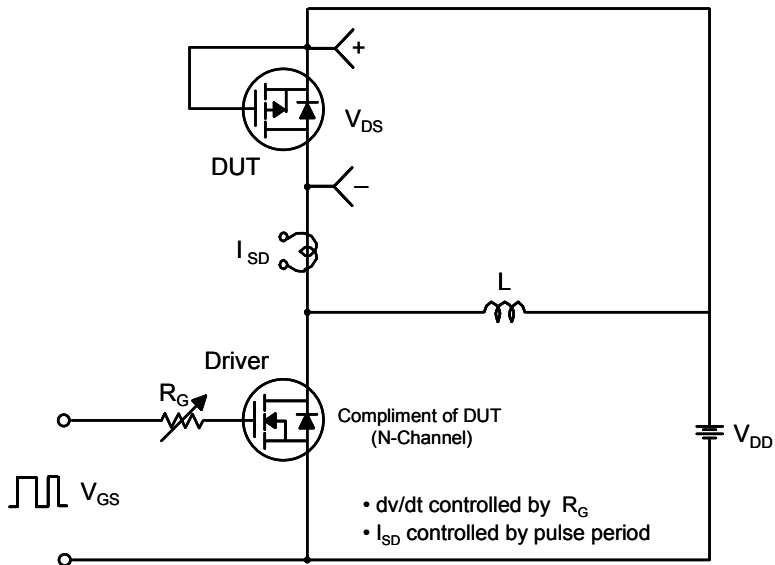
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms

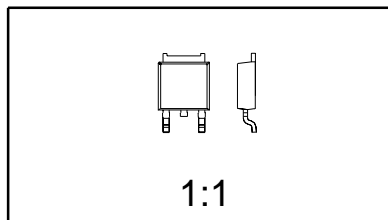
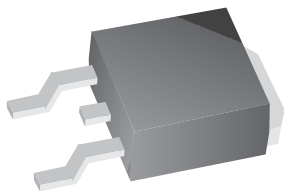


Peak Diode Recovery dv/dt Test Circuit & Waveforms



Mechanical Dimensions

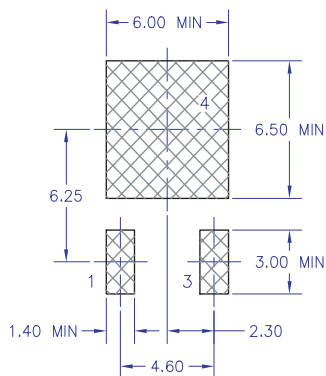
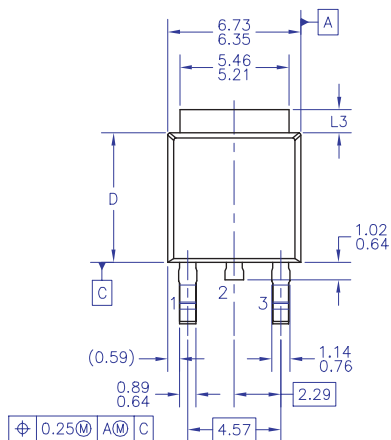
TO-252 (DPAK) (FS PKG Code 36)



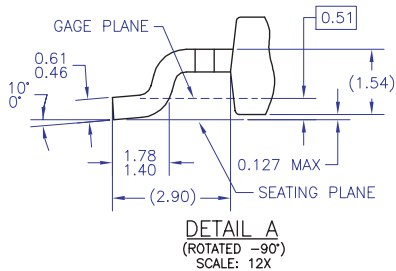
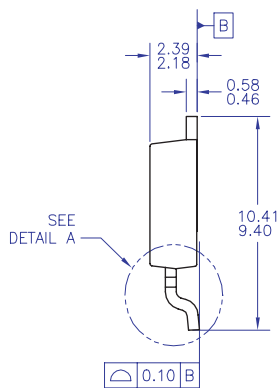
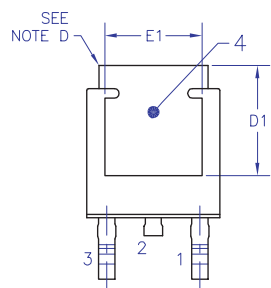
Scale 1:1 on letter size paper

Dimensions shown below are in:
millimeters

Part Weight per unit (gram): 0.33



LAND PATTERN RECOMMENDATION



NOTES: UNLESS OTHERWISE SPECIFIED

- A) ALL DIMENSIONS ARE IN MILLIMETERS.
- B) THIS PACKAGE CONFORMS TO JEDEC, TO-252, ISSUE C, VARIATION AA & AB, DATED NOV. 1999.
- C) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.
- D) HEAT SINK TOP EDGE COULD BE IN CHAMFERED CORNERS OR EDGE PROTRUSION.
- E) DIMENSIONS L3,D,E1&D1 TABLE:

	OPTION AA	OPTION AB
L3	0.89-1.27	1.52-2.03
D	5.97-6.22	5.33-5.59
E1	4.32 MIN	3.81 MIN
D1	5.21 MIN	4.57 MIN

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